

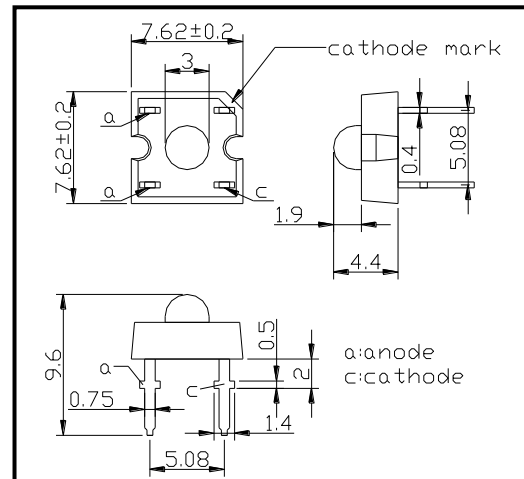
FL660-3532 High Power type LED

FL660-3532 is an AlGaInP LED mounted on a lead frame and molded with super beam lens. On forward bias, it emits a band of visible light which peaks 660nm.

◆ Specifications

- 1) Product Name Super Flux mold type LED
- 2) Type No. FL660-3532
- 3) Chip
 - (1) Chip Material AlGaInP
 - (2) Chip Dimension 350um*350um
 - (3) Peak Wavelength 660nm typ.
- 4) Package
 - (1) Type Super Beam type LED
 - (2) Resin Material Epoxy Resin
 - (3) Lead Frame Silver Plated Copper

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	200	mW	T _a =25°C
Forward Current	I _F	70	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Thermal Resistance	R _{thja}	120	K/W	
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =70mA		2.50	2.90	V
		I _F =50mA		2.40	2.80	
Total Radiated Power	P _O	I _F =70mA	35.0	52.0		mW
		I _F =50mA	25.0	35.0		
Radiant Intensity	I _E	I _F =70mA		65		mW/sr
Brightness	I _v	I _F =70mA		5300		mcd
Peak Wavelength	λ _P	I _F =50mA		660		nm
Dominant Wavelength	λ _D	I _F =50mA		642		
Half Width	Δλ	I _F =50mA		15		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		±20		deg.

‡Total Radiated Power is measured by S3584-08.

‡Radiant Intensity and Brightness is measured by Tektronix J-6512.